

TPD2E2U06 双通道高速 ESD 保护器件

1 特性

- IEC 61000-4-2 4 级
 - $\pm 25\text{kV}$ (接触放电)
 - $\pm 30\text{kV}$ (气隙放电)
- IEC 61000-4-5 浪涌保护
 - 5.5A 峰值脉冲电流 (8/20 μs 脉冲)
- IO 电容值 1.5pF (典型值)
- 直流 (DC) 击穿电压 6.5V (最小值)
- 超低泄漏电流 10nA (最大值)
- 低 ESD 钳位电压
- 工业温度范围: -40°C 至 $+125^{\circ}\text{C}$
- 小型易于走线的 DRL 封装

2 应用

- 终端设备
 - 机顶盒
 - 笔记本电脑
 - 服务器
 - 电子销售点 (EPOS)
- 接口
 - USB 2.0
 - 以太网
 - 移动产业处理器接口 (MIPI) 总线
 - 低压差分信令 (LVDS)
 - I2C

3 说明

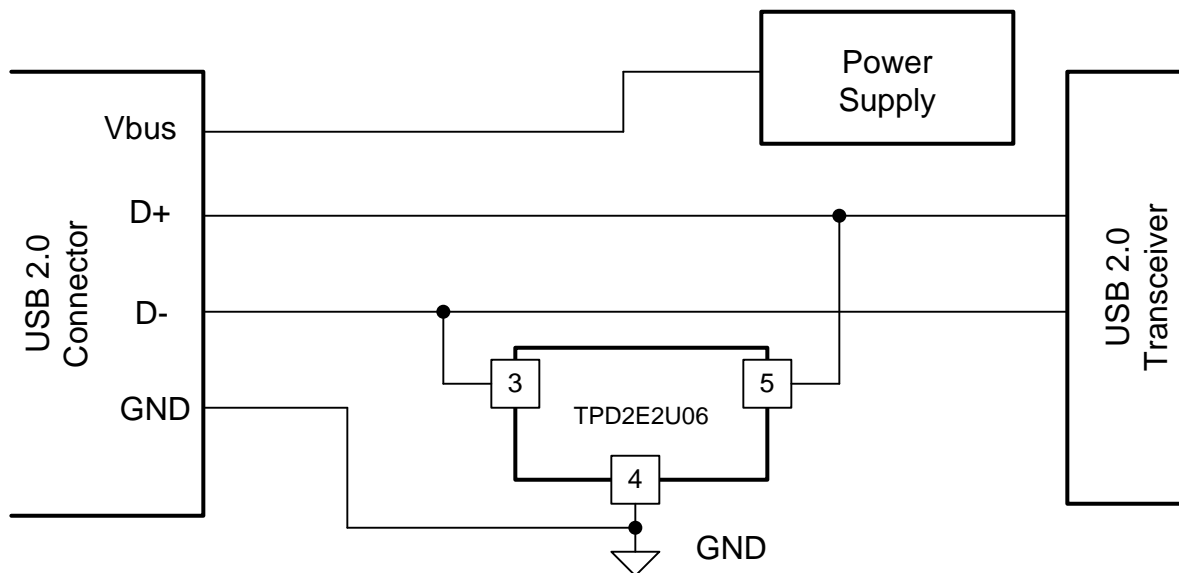
TPD2E2U06 是一款双通道低电容瞬态电压抑制器 (TVS) 二极管静电放电 (ESD) 保护器件。该器件可提供符合 IEC 61000-4-2 标准的 $\pm 25\text{kV}$ 接触 ESD 保护和 $\pm 30\text{kV}$ 气隙 ESD 保护。TPD2E2U06 的 1.5pF 线路电容使得此器件适合于广泛应用。典型应用接口为 USB 2.0, 低压差分信令 (LVDS) 接口和 I²C™。

器件信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
TPD2E2U06	SOT (5)	1.60mm x 1.20mm

(1) 要了解所有可用封装, 请见数据表末尾的可订购产品附录。

4 简化电路原理图



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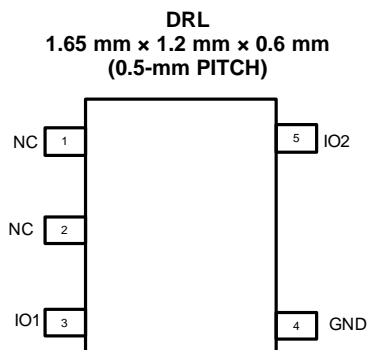
5 修订历史记录

Changes from Revision A (June 2013) to Revision B

Page

- 已添加 ESD 额定值表，特性描述部分，器件功能模式，应用和实施部分，电源相关建议部分，布局部分，器件和文档支持部分以及机械、封装和可订购信息部分。 **1**

6 Pin Configuration and Functions



Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
IO1	3	I/O	The IO1 and IO2 pins are an ESD protected channel. Connect these pins to the data line as close to the connector as possible.
IO2	5	I/O	
NC	1, 2	-	This pin is not connected and is left floating, grounded, or connected to VCC.
GND	4	G	The GND (ground) pin is connected to ground.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
I_{PP} Peak pulse current (tp = 8/20 μ s)		5.5 ⁽¹⁾	A
P_{PP} Peak pulse power (tp = 8/20 μ s)		85 ⁽¹⁾	W
Operating temperature	-40	125	°C
Storage temperature	-65	155	°C

(1) Measured at 25°C.

7.2 ESD Ratings

		VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 ⁽²⁾	±1500	
	EC 61000-4-2 contact	±25000	
	EC 61000-4-2 air-gap	±30000	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 500-V HBM is possible with the necessary precautions.

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process. Manufacturing with less than 250-V CDM is possible with the necessary precautions.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_{IO}	Input Pin Voltage	0		5.5	V
T_A	Operating Free Air Temperature	-40		125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPD2E2U06		UNIT
		DRL		
		5 PINS		
R _{θJA}	Junction-to-ambient thermal resistance	286.8		°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	130.7		
R _{θJB}	Junction-to-board thermal resistance	104.8		
ψ _{JT}	Junction-to-top characterization parameter	25.6		
ψ _{JB}	Junction-to-board characterization parameter	104.3		

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

7.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
V _{RWM}	Reverse stand-off voltage	I _{IO} < 10 μA			5.5	V
V _{CLAMP}	IO to GND	I _{PP} = 1 A, TLP ⁽¹⁾		9.7		V
		I _{PP} = 5 A, TLP ⁽¹⁾		12.4		
V _{CLAMP}	GND to IO	I _{PP} = 1 A, TLP ⁽¹⁾		1.9		V
		I _{PP} = 5 A, TLP ⁽¹⁾		4		
R _{DYN}	Dynamic resistance	IO to GND ⁽²⁾		0.5		Ω
R _{DYN}	Dynamic resistance	GND to IO ⁽²⁾		0.25		Ω
CL	Line capacitance	f = 1 MHz, V _{BIAS} = 2.5 V ⁽³⁾		1.5	1.9	pF
C _{CROSS}	Channel-to-channel input capacitance	Pin 4 = 0 V, f = 1 MHz, V _{BIAS} = 2.5 V, between channel pins ⁽³⁾		0.02	0.03	pF
ΔC _{IO-TO-GND}	Variation of channel input capacitance	Pin 4 = 0 V, f = 1 MHz, V _{BIAS} = 2.5 V, channel_x pin to GND – channel_y pin to GND ⁽³⁾		0.03	0.1	pF
V _{BR}	Break-down voltage	I _{IO} = 1 mA	6.5		8.5	V
I _{LEAK}	Leakage current	V _{IO} = 2.5 V		1	10	nA

(1) Transmission Line Pulse with 10-ns rise time, 100-ns width.

(2) Extraction of R_{DYN} Using least squares fit of TLP characteristics between I = 20 A and I = 30 A.

(3) Measured at 25°C.

7.6 Typical Characteristics

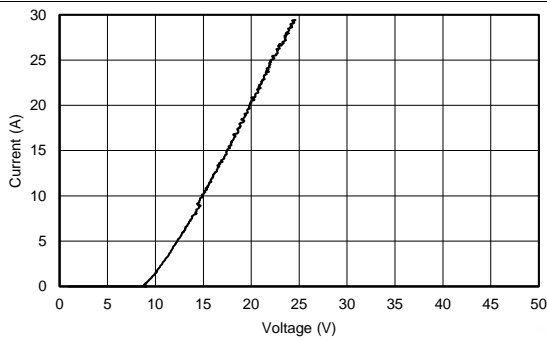


Figure 1. TLP, Data to GND

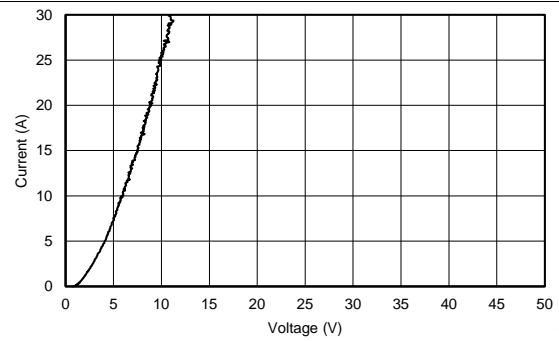


Figure 2. TLP, GND to Data

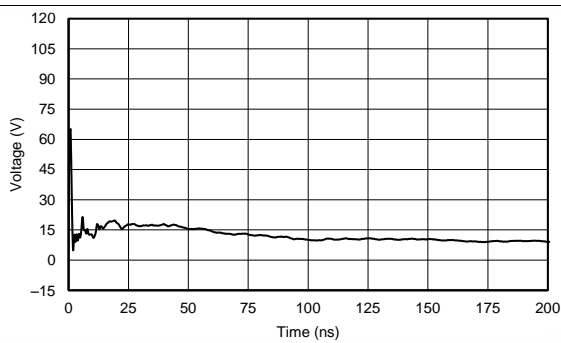


Figure 3. IEC 61000-4-2 Clamping Voltage, +8 kV Contact

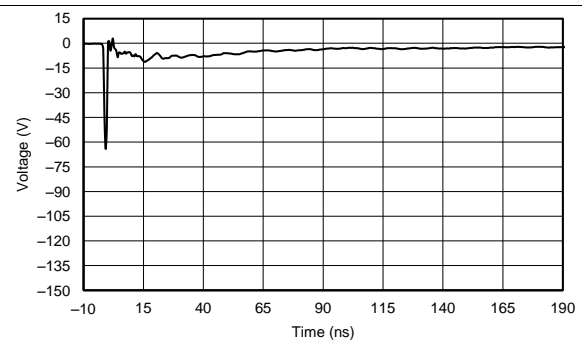
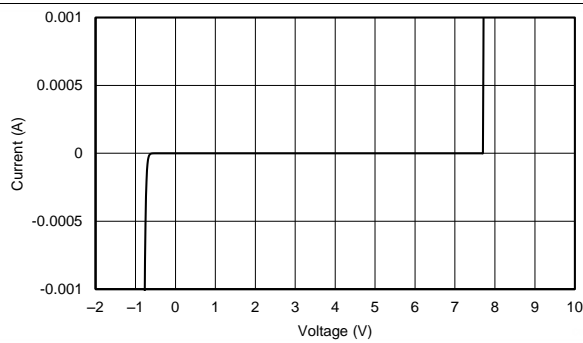
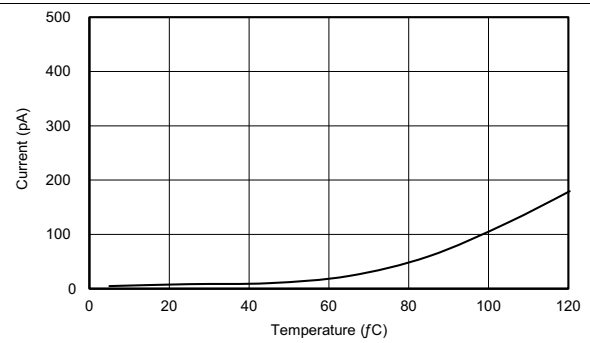


Figure 4. IEC 61000-4-2 Clamping Voltage, -8 kV Contact



$T_A = 25^\circ\text{C}$

Figure 5. IV Curve



$V_{IN} 2.5\text{ V}$

Figure 6. I_{LEAK} vs Temperature

Typical Characteristics (continued)

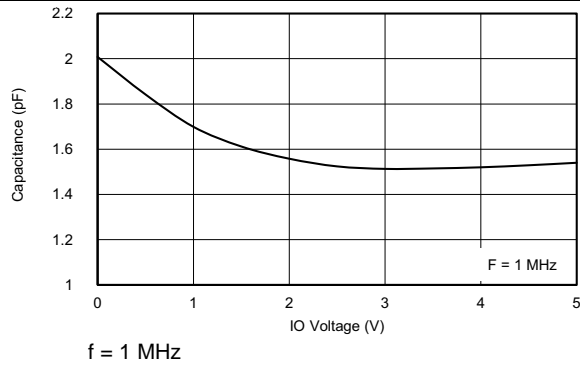


Figure 7. Capacitance Across V_{BIAS}

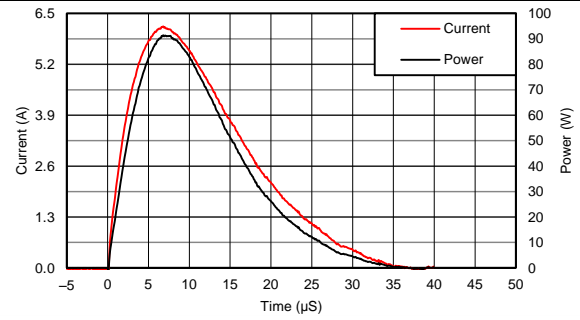


Figure 8. Surge Curve (tp = 8/20 μs) IO to GND

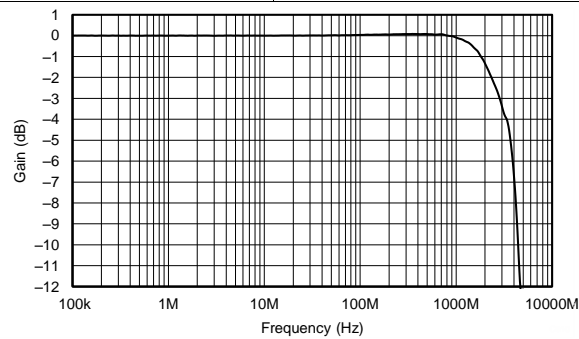


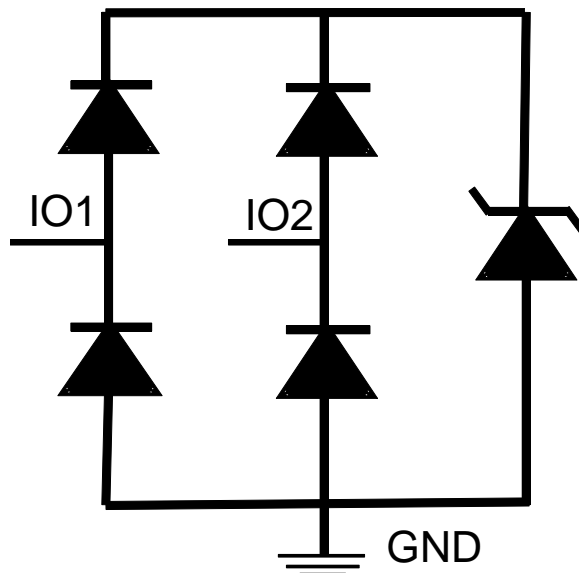
Figure 9. Insertion Loss

8 Detailed Description

8.1 Overview

The TPD2E2U06 is a dual-channel low capacitance TVS diode ESD protection device. The device offers ± 25 -kV contact and ± 30 -kV air-gap ESD protection in accordance with the IEC 61000-4-2 standard. The 1.5-pF line capacitance of the TPD2E2U06 makes the device suitable for a wide range of applications. Typical application interfaces are USB 2.0, LVDS, and I2C.

8.2 Functional Block Diagram



8.3 Feature Description

The TPD2E2U06 is a dual-channel low capacitance TVS diode ESD protection device. The device offers ± 25 -kV contact and ± 30 -kV air-gap ESD protection in accordance with the IEC 61000-4-2 standard. The 1.5-pF line capacitance of the TPD2E2U06 makes the device suitable for a wide range of applications. Typical application interfaces are USB 2.0, LVDS, and I2C.

8.3.1 IEC 61000-4-2 Level 4

The I/O pins can withstand ESD events up to ± 25 -kV contact and ± 30 -kV air. An ESD/surge clamp diverts the current to ground.

8.3.2 IO Capacitance

The capacitance between each I/O pin to ground is 1.5 pF. These capacitances support data rates in excess of 1.5 Gbps.

8.3.3 DC Breakdown Voltage

The DC breakdown voltage of each I/O pin is a minimum of 6.5 V. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of 5.5 V.

8.3.4 Ultra-Low Leakage Current

The I/O pins feature an ultra-low leakage current of 10 nA (Max) with a bias of 2.5 V.

8.3.5 Low ESD Clamping Voltage

The I/O pins feature an ESD clamp that is capable of clamping the voltage to 9.7 V ($I_{PP} = 1$ A).

Feature Description (continued)

8.3.6 Industrial Temperature Range

This device is designed to operate from -40°C to 125°C .

8.3.7 Small Easy-to-Route Package

The layout of this device makes it simple and easy to add protection to an existing layout. The packages offers flow-through routing, requiring minimal modification to an existing layout.

8.4 Device Functional Modes

TPD2E2U06 is a passive integrated circuit that triggers when voltages are above V_{BR} or below the lower diodes V_f (-0.6 V). During ESD events, voltages as high as $\pm 30\text{ kV}$ (air) can be directed to ground via the internal diode network. Once the voltages on the protected line fall below the trigger levels of TPD2E2U06 (usually within 10's of nano-seconds) the device reverts to passive.

9 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

TPD2E2U06 is a diode type TVS which is typically used to provide a path to ground for dissipating ESD events on hi-speed signal lines between a human interface connector and a system. As the current from ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low R_{DYN} of the triggered TVS holds this voltage, V_{CLAMP} , to a safe level for the protected IC.

9.2 Typical Application

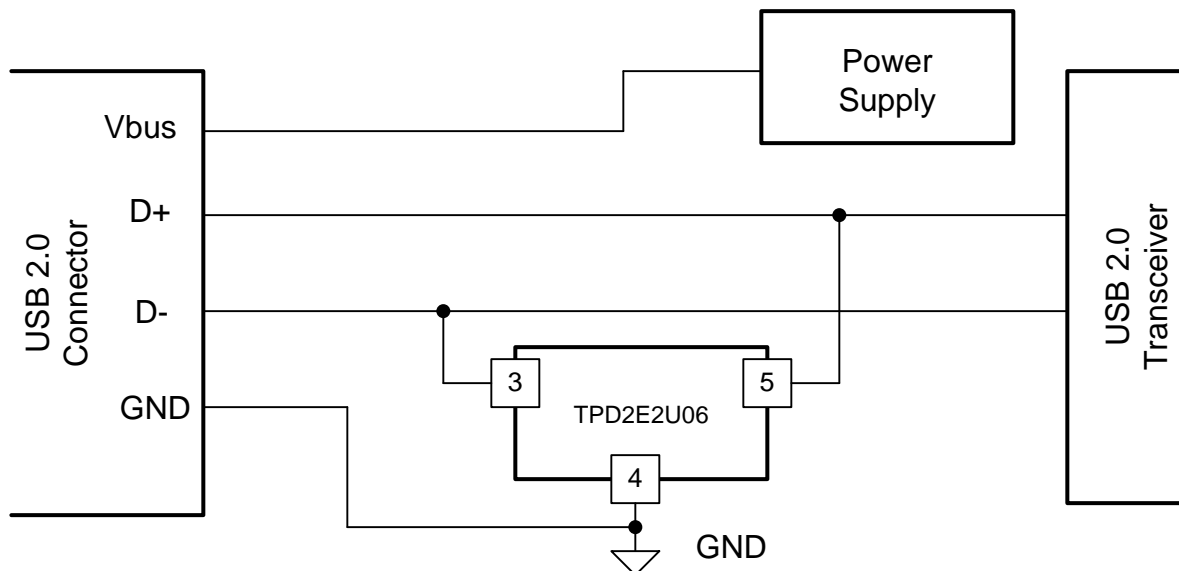


Figure 10. Typical USB Application Diagram

9.2.1 Design Requirements

For this design example, one TPD2E2U06 device will be used in a USB 2.0 application. This will provide complete port protection.

Given the USB 2.0 application, the following parameters are known.

DESIGN PARAMETER	VALUE
Signal range on Pins 3 or 5	0 V to 3.3 V
Operating Frequency	240 MHz

9.2.2 Detailed Design Procedure

To begin the design process, some parameters must be decided upon; the designer needs to know the following:

- Signal range of all the protected lines
- Operating frequency

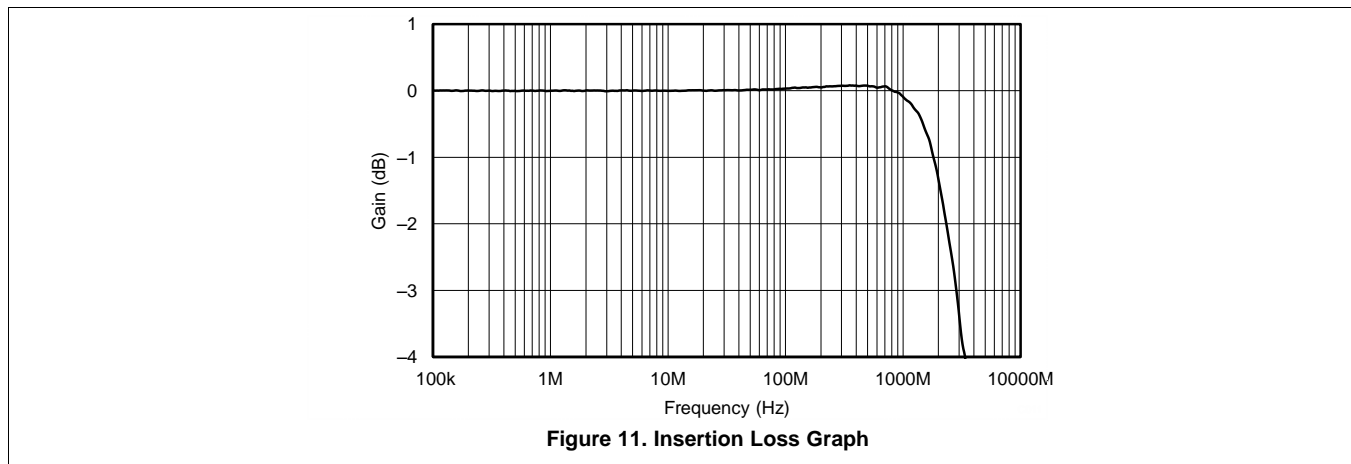
9.2.2.1 Signal Range

The TPD2E2U06 has 2 identical protection channels for signal lines. The symmetry of the device provides flexibility when selecting which of the 2 I/O channels will protect which signal lines. Any I/O will support a signal range of 0 to 5.5 V.

9.2.2.2 Operating Frequency

The TPD2E2U06 has a capacitance of 1.5 pF (Typ), supporting USB 2.0 data rates.

9.2.3 Application Curves



10 Power Supply Recommendations

This device is a passive ESD protection device and there is no need to power it. Care should be taken to make sure that the maximum voltage specifications for each line are not violated.

11 Layout

11.1 Layout Guidelines

- The optimum placement is as close to the connector as possible.
 - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
 - The PCB designer needs to minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
 - Electric fields tend to build up on corners, increasing EMI coupling.

11.2 Layout Example

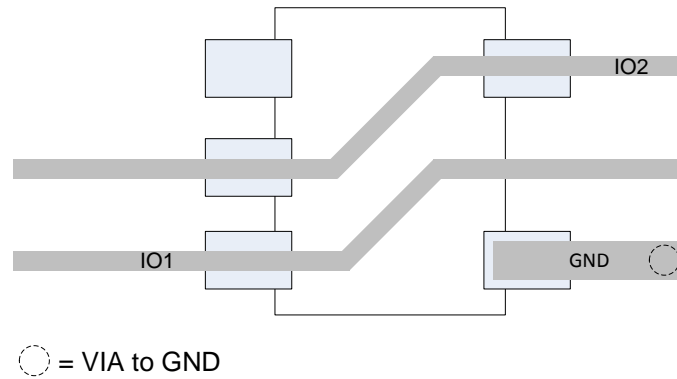


Figure 12. Routing with DRL Package

12 器件和文档支持

12.1 商标

I²C is a trademark of NXP Semiconductors.
All other trademarks are the property of their respective owners.

12.2 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.3 术语表

[SLYZ022](#) — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

13 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPD2E2U06DRLR	ACTIVE	SOT-5X3	DRL	5	4000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	DT	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TPD2E2U06 :

- Automotive: [TPD2E2U06-Q1](#)

NOTE: Qualified Version Definitions:

- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

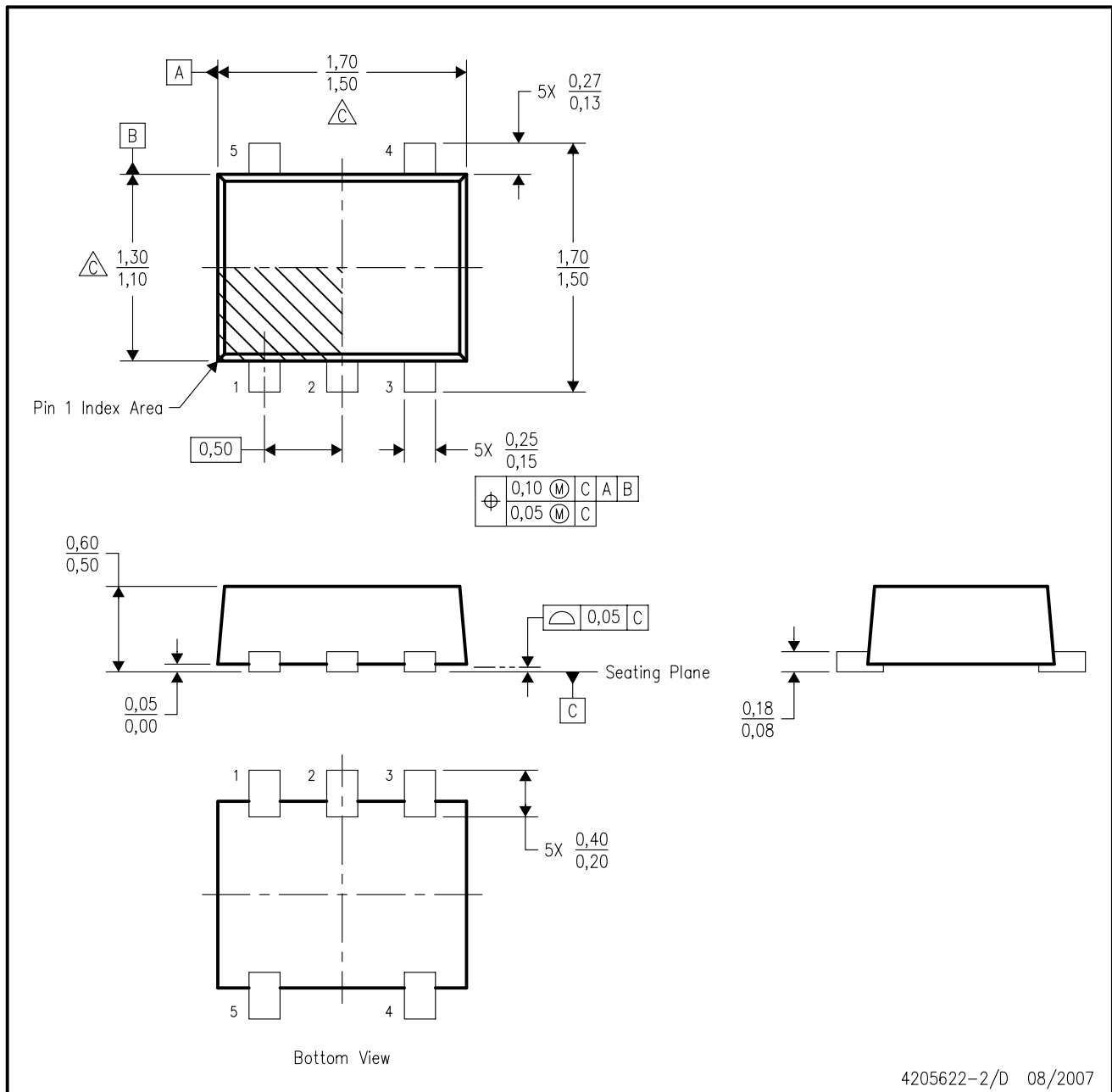
Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPD2E2U06DRLR	SOT-5X3	DRL	5	4000	180.0	8.4	1.98	1.78	0.69	4.0	8.0	Q3

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPD2E2U06DRLR	SOT-5X3	DRL	5	4000	183.0	183.0	20.0



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- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash, interlead flash, protrusions, or gate burrs. Mold flash, interlead flash, protrusions, or gate burrs shall not exceed 0,15 per end or side.
 - D. JEDEC package registration is pending.

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